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Fairchild Semiconductor MMBT3904T

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MMBT3904T NPN Epitaxial Silicon Transistor

Features

- General purpose amplifier transistor.
- Ultra-Small Surface Mount Package for all types.
- Suitable for general switching & amplification
- · Well suited for portable application
- As complementary type, PNP MMBT3906T is recommended

Absolute Maximum Ratings T_a = 25°C unless otherwise noted

| Symbol | Parameter | Value | Unit |
|------------------|---------------------------|-----------|------|
| V _{CBO} | Collector-Base Voltage | 60 | V |
| V _{CEO} | Collector-Emitter Voltage | 40 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| С | Collector Current | 200 | mA |
| Г _Ј | Junction Temperature | 150 | °C |
| Т _{STG} | Storage Temperature Range | -55 ~ 150 | ۵° |

of anv semiconductor device mav These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics* Ta=25°C unless otherwise noted

| Symbol | Parameter | Max | Unit |
|-----------------|---|-----|------|
| P _C | Collector Power Dissipation, by $R_{\theta JA}$ | 250 | mW |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 500 | °C/W |

Minimum land pad.

Electrical Characteristics* T_a=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Unit |
|-----------------------|--------------------------------------|--|-----------------------------|--------------|--------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_{C} = 10 \mu A, I_{E} = 0$ | 60 | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_{\rm C} = 1 {\rm mA}, \ I_{\rm B} = 0$ | 40 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_{E} = 10 \mu A, I_{C} = 0$ | 6 | | V |
| I _{CEX} | Collector Cut-off Current | $V_{CE} = 60V, V_{EB(OFF)} = 3V$ | | 50 | nA |
| h _{FE} | DC Current Gain | $V_{CE} = 1V, I_{C} = 0.1mA$ $V_{CE} = 1V, I_{C} = 1mA$ $V_{CE} = 1V, I_{C} = 10mA$ $V_{CE} = 1V, I_{C} = 50mA$ $V_{CE} = 1V, I_{C} = 100mA$ | 40 70 100 60 30 | 300 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | $I_{C} = 10$ mA, $I_{B} = 1$ mA $I_{C} = 50$ mA, $I_{B} = 5$ mA | | 0.2 0.3 | V V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_{C} = 10$ mA, $I_{B} = 1$ mA $I_{C} = 50$ mA, $I_{B} = 5$ mA | 0.65 | 0.85 0.95 | V V |
| f _T | Current Gain Bandwidth Product | V _{CE} = 20V, I _C = 10mA, f = 100MHz | 300 | | MHz |
| C _{ob} | Output Capacitance | $V_{CB} = 5V, I_E = 0, f = 1MHz$ | | 6 | pF |
| C _{ib} | Input Capacitance | $V_{EB} = 0.5V, I_{C} = 0, f = 1MHz$ | | 15 | pF |
| t _d | Delay Time | $V_{CC} = 3V, I_{C} = 10mA$ | | 35 | ns |
| t _r | Rise Time | I _{B1} =- I _{B2} = 1mA | | 35 | ns |
| t _s | Storage Time | | | 200 | ns |
| t _f | Fall Time | | | 50 | ns |

* DC Item are tested by Pulse Test : Pulse Width≤300us, Duty Cycle≤2%

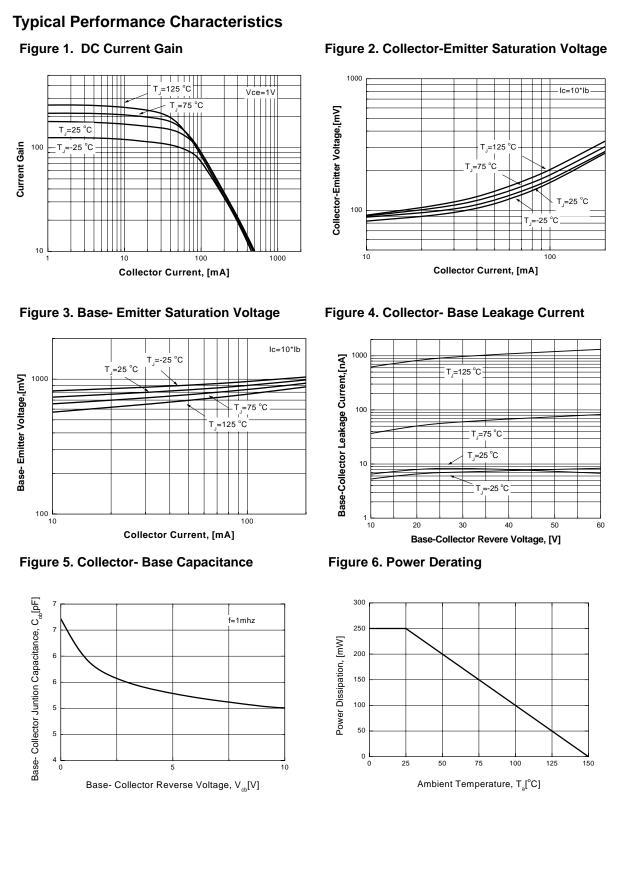


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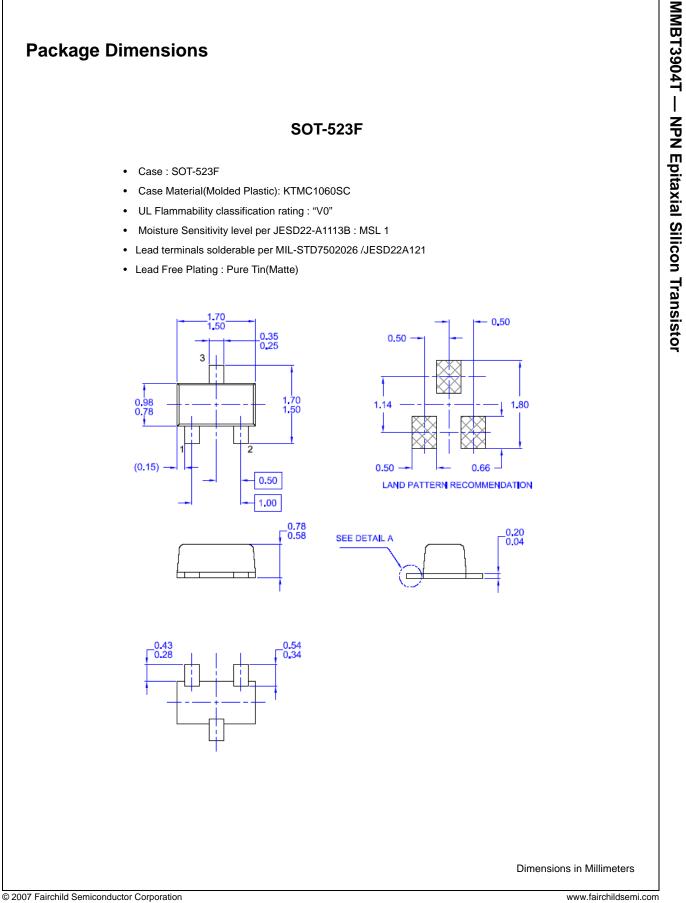
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| PRODUCT | STATUS | DEFINITIONS |
|---------|--------|-------------|
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| Datasheet Identification | Product Status | Definition |
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